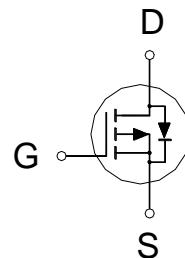


NIKO-SEM**P-Channel Logic Level Enhancement Mode
Field Effect Transistor****PK5C1BA
PDFN 5x6P
Halogen-Free & Lead-Free****PRODUCT SUMMARY**

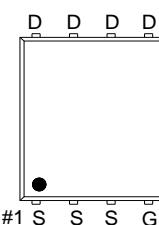
$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
-40V	5.1mΩ	-74A

**Features**

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.



G. GATE
D. DRAIN
S. SOURCE

100% UIS Tested
100% Rg Tested

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	± 25	V
Continuous Drain Current ⁴	$T_C = 25^\circ\text{C}$	I_D	-74	A
	$T_C = 100^\circ\text{C}$		-47	
	$T_A = 25^\circ\text{C}$		-20	
	$T_A = 70^\circ\text{C}$		-16	
Pulsed Drain Current ¹		I_{DM}	-160	
Avalanche Current		I_{AS}	-62	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	192	mJ
Power Dissipation ³	$T_C = 25^\circ\text{C}$	P_D	54	W
	$T_C = 100^\circ\text{C}$		21	
	$T_A = 25^\circ\text{C}$		4.1	
	$T_A = 70^\circ\text{C}$		2.6	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

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THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10s$	$R_{\theta JA}$		30	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		51	
Junction-to-Case	Steady-State	$R_{\theta JC}$		2.3	

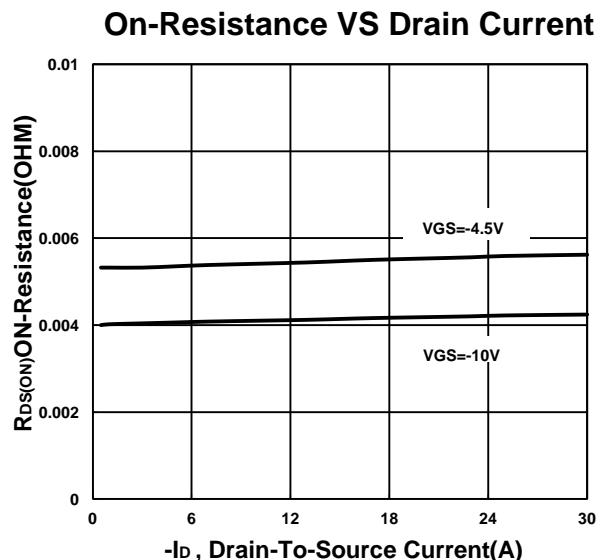
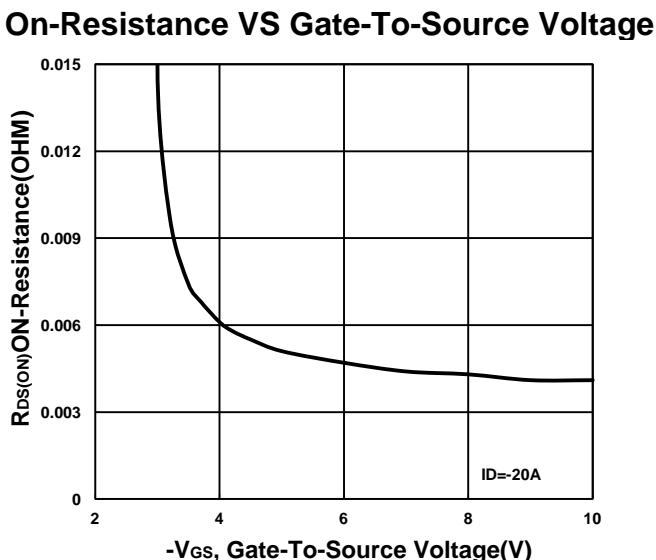
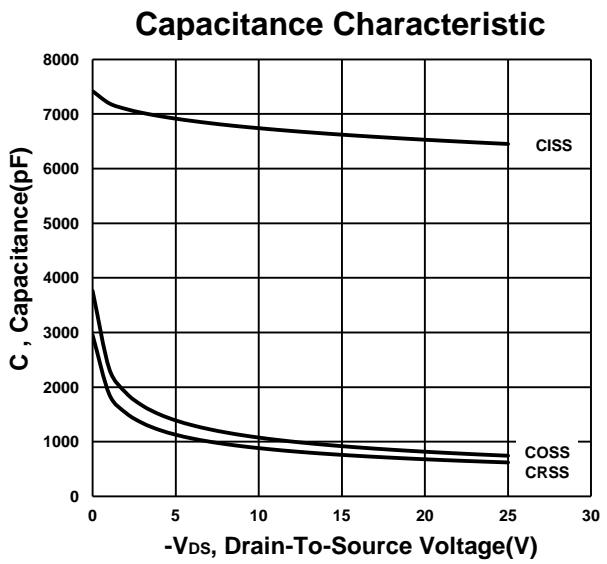
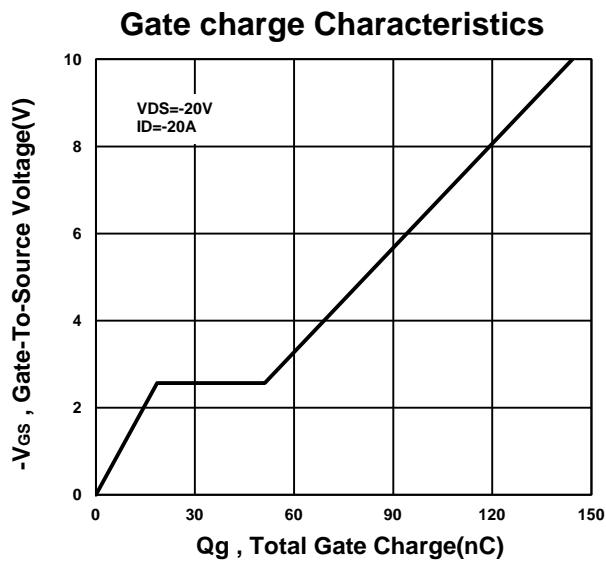
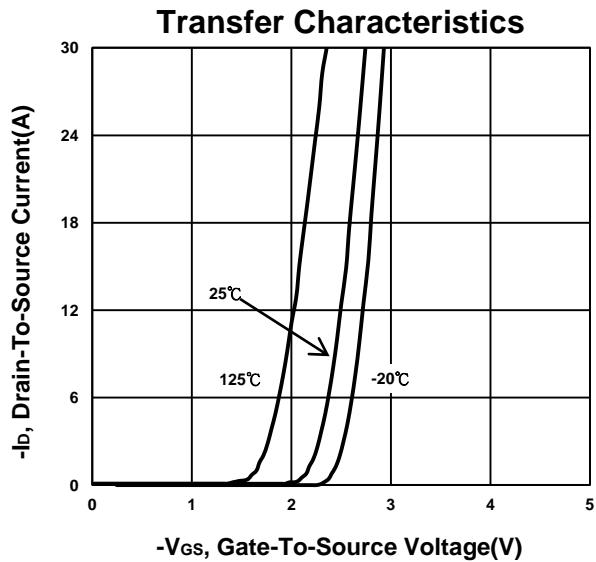
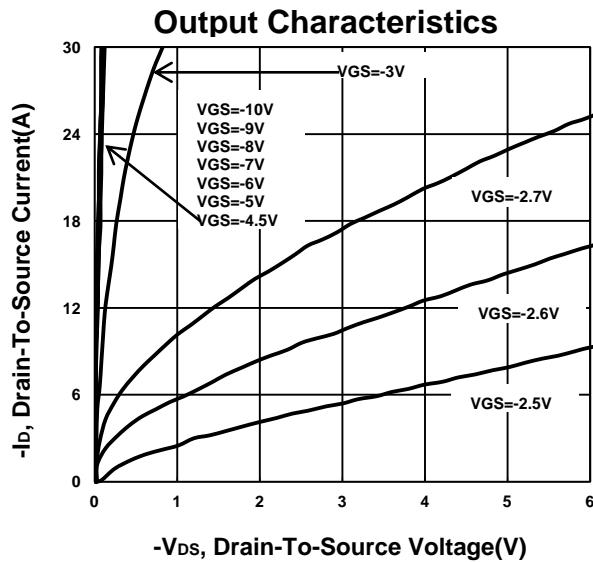
¹Pulse width limited by maximum junction temperature.²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$. The value in any given application depends on the user's specific board design.³The Power dissipation is based on $R_{\theta JA} t \leq 10s$ value.⁴Package limitation current is -51A.**ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ C$, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.3	-1.8	-2.3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 25V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -32V, V_{GS} = 0V$			-1	uA
		$V_{DS} = -30V, V_{GS} = 0V, T_J = 125^\circ C$			-10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -20A$		3.9	5.1	$m\Omega$
		$V_{GS} = -4.5V, I_D = -15A$		5.3	7.5	
Forward Transconductance ¹	g_f	$V_{DS} = -5V, I_D = -20A$		72		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -20V, f = 1MHz$		6538		pF
Output Capacitance	C_{oss}			818		
Reverse Transfer Capacitance	C_{rss}			683		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		3.8		Ω
Total Gate Charge ²	Q_g	$V_{DS} = -20V, V_{GS} = -10V, I_D = -20A$		144		nC
Gate-Source Charge ²	Q_{gs}			18.5		
Gate-Drain Charge ²	Q_{gd}			32		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = -20V, I_D \approx -20A, V_{GS} = -10V, R_{GS} = 6\Omega$		20		nS
Rise Time ²	t_r			49		
Turn-Off Delay Time ²	$t_{d(off)}$			291		
Fall Time ²	t_f			173		

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SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)						
Continuous Current ³	I_S				-41	A
Forward Voltage ¹	V_{SD}	$I_F = -20\text{A}, V_{GS} = 0\text{V}$			-1.3	V
Reverse Recovery Time	t_{rr}	$I_F = -20\text{A}, dI_F/dt = 100 \text{ A / } \mu\text{s}$		39		nS
Reverse Recovery Charge	Q_{rr}			27		nC

¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.³Package limitation current is -51A.

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